

Extraction of Schottky diode parameters from forward

Applied Physics Letters

49, 85-87

DOI: 10.1063/1.97359

Citation Report

#	ARTICLE	IF	CITATIONS
10	Transition from Schottky barriers to p-n junctions. Solid-State Electronics, 1987, 30, 719-722.	0.8	7
11	Determination of the doping profile near the metal-semiconductor interface of ZrN/GaAs contacts. IEEE Transactions on Electron Devices, 1988, 35, 1384-1386.	1.6	1
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